IN THE TITLE:

Please delete the title SYSTEM AND METHOD FOR OXONE CLEANING A LIQUID CRYSTAL DISPLAY STRUCTURE and substitute therefor the title SYSTEM AND METHOD FOR FORMING OZONE RESISTANT IC AND LCD STRUCTURES.

IN THE CLAIMS:

Please cancel claim 2, 3, 19, 20, and 25.

Please amend claims 1, 8, 18, 22, and 24 as follows.

1. (Currently Amended) In the fabrication of integrated circuit (IC) structures, a method for forming a structure resistant to ozone stripping, the method comprising:

forming a first electrically conducting layer from indium tin oxide (ITO);

forming an ozone resistant barrier overlying the first electrically conducting layer from a material selected from the group including Ta, Ti, TaN, Al, Al compounds, tungsten, and copper; and,

forming a metal layer overlying the ozone resistive barrier.

4. (Original) The method of claim 1 wherein forming a metal layer overlying the ozone resistant barrier includes forming a reflective metal layer from Al.

5. (Original) The method of claim 4 wherein forming a metal layer overlying the ozone resistant barrier includes forming a layer of Al having a thickness of greater than 1000 Å.

6. (Original) The method of claim 1 in which a reflective liquid crystal display (LCD) IC structure is formed;

wherein forming a first electrically conducting layer includes forming an electrode; and,

wherein forming a metal layer overlying the ozone resistant barrier includes forming an LCD reflector.

7. (Original) The method of claim 1 in which a busline IC structure is formed; and,

wherein forming a metal layer overlying the ozone resistant barrier includes forming the top metal layer of a busline.

8. (Currently Amended) In the fabrication of liquid crystal displays (LCDs) integrated circuits (ICs), a method for forming a LCD structure resistant to ozone stripping, the method comprising:

forming an indium tin oxide (ITO) layer electrode;

forming an ozone resistant barrier overlying the electrode from a material selected from the group including Ti, Ta, ~~TiN,~~ and TaN; and,

forming an Al reflector overlying the ozone resistant barrier.

18. (Currently Amended) A liquid crystal display (LCD) reflector structure resistant to ozone stripping, the reflector structure comprising:

a first electrically conducting layer of indium tin oxide (ITO);

an ozone resistive barrier overlying the first electrically conducting layer from a material selected from the group including Ti, Ta, TaN, Al, Al compounds, tungsten, and copper; and,

a metal layer overlying the ozone resistive barrier.

21. (Original) The reflector structure of claim 18 wherein the metal layer is a reflective metal layer material selected from the group including Al.

22. (Currently Amended) A liquid crystal display (LCD) reflector structure resistant to ozone stripping, the reflector structure comprising:

a first electrically conducting layer of indium tin oxide (ITO);

an ozone resistive barrier overlying the first electrically conducting layer selected from the group including Ti, Ta, ~~TiN,~~ TaN, Al, Al compounds, tungsten, ~~chrome,~~ and copper; and,

an Al reflective metal layer overlying the ozone resistive barrier.

23. (Original) A liquid crystal display (LCD) reflector structure resistant to ozone stripping, the reflector structure comprising:

a first electrically conducting layer selected from the group including Ti, Ta, and Al; and,

a reflective metal layer overlying the first electrically conducting layer selected from the group including Al.

24. (Currently Amended) In the fabrication of integrated circuit (IC) structures, a method for forming a structure resistant to ozone stripping, the method comprising:

forming a first electrically conducting layer from a material selected from the group including Ti, Ta, and Al; and,

forming a metal layer overlying the electrically conducting layer.

26. (Original) The method of claim 24 wherein forming a metal layer overlying the first electrically conducting layer includes forming a reflective metal layer from Al.

27. (Original) The method of claim 26 wherein forming a metal layer overlying the first electrically conducting layer includes forming a layer of Al having a thickness of greater than 1000 Å.

28. (Original) The method of claim 24 in which a reflective liquid crystal display (LCD) IC structure is formed;

wherein forming a first electrically conducting layer includes forming an electrode; and,

wherein forming a metal layer overlying the first electrically conducting layer includes forming an LCD reflector.

29. (Original) The method of claim 24 in which a busline IC structure is formed; and,

wherein forming a metal layer overlying the first electrically conducting layer includes forming the top metal layer of a busline.